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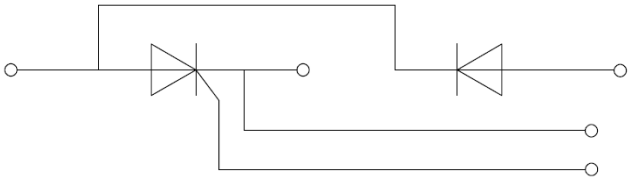

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FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

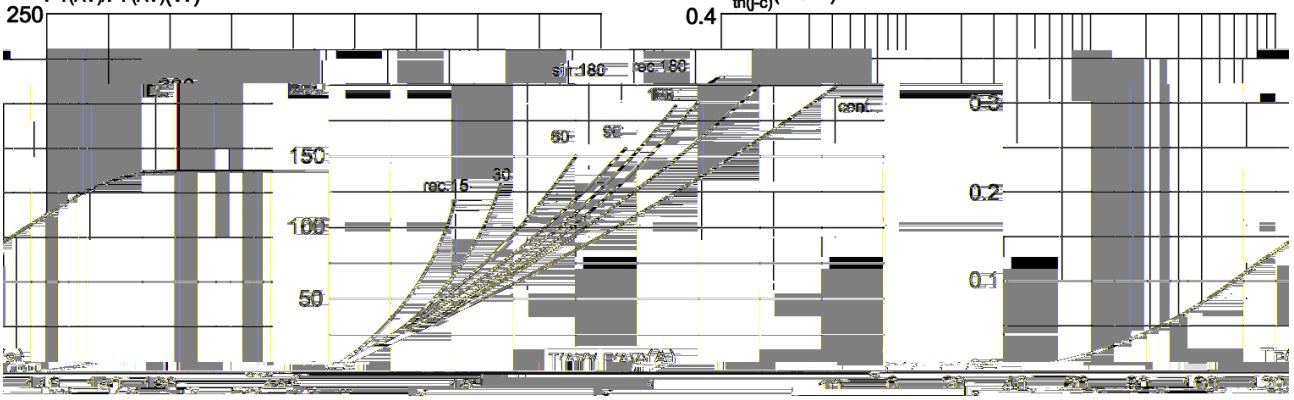

FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

FIG.3: Forward characteristics (per thyristor or diode)

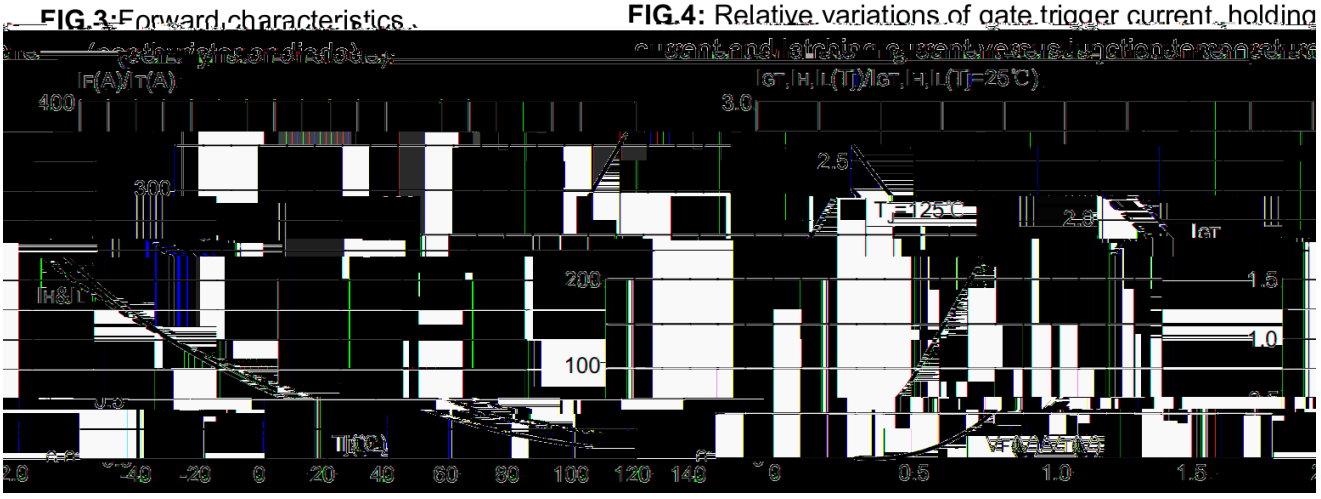

FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

case temperature
de)

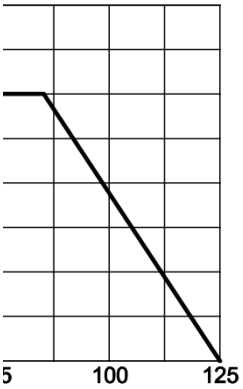

FIG.5 Gate trigger characteristics

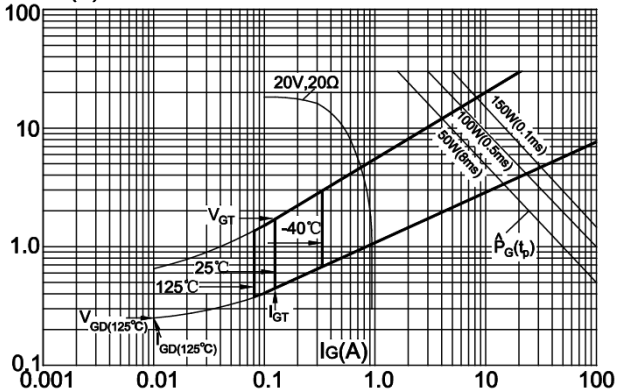

FIG.6: Forward current vs. (per thyristor or dioc

